















**ESD** 

TVS

MOS

LDO

Diode

Sensor

DC-DC

# **Product Specification**

Domestic Part Number	SI2303
<ul><li>Overseas Part Number</li></ul>	SI2303
▶ Equivalent Part Number	SI2303





# SOT-23 Plastic-Encapsulate MOSFETS

# SI2303 P-channel 30-V(D-S) MOSFET

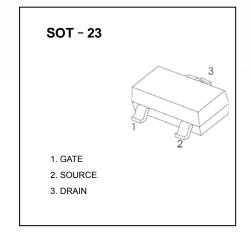
V(BR)DSS	RDS(on)MAX	ID
-30 V	190mΩ@-10V	-1.7A
-30 V	330mΩ@-4.5V	-1.7A

#### **FEATURE**

**X TrenchFET Power MOSFET** 

#### **APPLICATION**

- Load Switch for Portable Devices
- DC/DC Converter



#### **MARKING**

### **Equivalent Circuit**





#### Maximum ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	-30	V
Gate-Source Voltage	VGS	±20	٧
Continuous Drain Current	ID	-1.7	
Pulsed Diode Curren	IDM	-10	Α
Continuous Source-Drain Current(Diode Conduction)	IS	-1	
Power Dissipation	PD	0.9	W
Thermal Resistance from Junction to Ambient (t≤5s)	RθJA	357	°C/W
Operating Junction	TJ	150	$^{\circ}$
Storage Temperature	TSTG	-55~+150	$^{\circ}$



### SOT-23 Plastic-Encapsulate MOSFETS

#### **MOSFET ELECTRICAL CHARACTERISTICS**

Static Electrical Characteristics (Ta = 25  $^{\circ}$ C Unless Otherwise Noted)

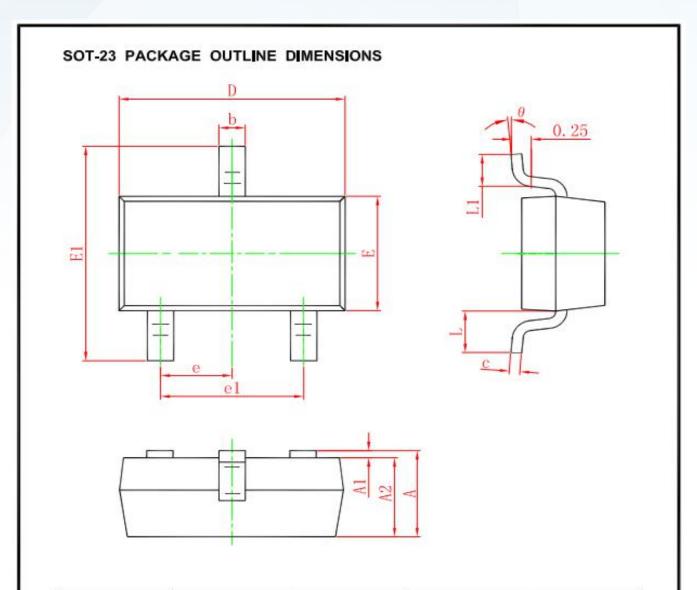
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = -250μA	-30			V
Gate-source threshold voltage	VGS(th)	VDS =VGS, ID = -250μA	-1		-3	V
Gate-source leakage	IGSS	VDS =0V, VGS = ±20V			±100	nA
Zero gate voltage drain current	IDSS	VDS = -30V, VGS =0V			-1	μΑ
Drain-source on-state resistancea		VGS = -10V, ID = -1.7A		120	190	mΩ
	RDS(on)	VGS = -4.5V, ID = -1.3A		150	330	mΩ
Forward transconductancea	gfs	VDS = -10V, ID = -1.7A	5.5			S
Diode forward voltage	VSD	IS=-1A,VGS=0V		-0.8	-1.2	V
Dynamic						
Input capacitance	Ciss			155		pF
Output capacitance	Coss	VDS = -15V, VGS =0V, f=1MHz		35		pF
Reverse transfer capacitanceb	Crss	1 1111112		25		pF
Total gate charge	Qg	VDS = -15V,		2	4	nC
Gate-source charge	Qgs	VDS = -15V, VGS = -4.5V,		0.6		nC
Gate-drain charge	Qgd	ID =-1.7A		1		nC
Gate resistance	Rg	f=1MHz		8.5	17	Ω
Switchingb		<u> </u>				
Turn-on delay time	td(on)			36	44	ns
Rise time	tr	VDD= -15V		37	45	ns
Turn-off delay time	td(off)	RL=10Ω, ID ≈ -1.5A, VGEN=- 4.5V,Rg=5Ω		12	18	ns
Fall time	tf			9	14	ns
Drain-source body diode cha	racteristic	es			•	
Continuous Source-Drain Diode Current	IS	Tc=25℃			-1.75	А
Pulsed Diode forward Curren	ISM				-10	Α

#### Note :

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t < 5 sec.
- 3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production testing.



# SOT-23 Plastic-Encapsulate MOSFETS



Complete	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP.	0.037 TYP.		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF.		0.022	REF.	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	



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